

Physics - ICS Part 2 Physics Chapter 18 Short Questions Preparation

Q1. Define Depletion region?

Ans 1: A region in a semiconductor device, usually at the junction of p-type and n-type materials, in which there is neither an excess of electrons nor of holes is called depletion region, it is a chargeless region.

Q2. What is meant by rectification?

Ans 1: The converting of alternating current signal into pulsating direct current signal is called rectification. The current for this purpose is called rectifier circuit.

Q3. How is p-n junction formed?

Ans 1: A p-n junction is formed when a crystal of germanium or silicon is grown in such a way that its one half is doped with a trivalent impurity and the other half with a pentavalent impurity.

Q4. What is the role of potential barrier in a diode? How is it formed in a diode?

Ans 1: At the formation of a p-n junction, the free electrons in the n-region, because of their random motion, diffuse into the p-region. As a result of this diffusion, a region is formed around the junction consisting of positive and negative ions. Due to the charge on these ions, a potential difference develops across the depletion region. This potential difference is called a potential barrier, which stops further diffusion of electrons into the p-region.

Q5. Why are charge carriers not present in the depletion region?

Ans 1: This is due to the fact that when an electron from the n-region diffuses into the p-region, it leaves behind a positive ion. When this electron recombines with the hole in the p-region, a negative ion is formed. So, no charge carriers are available in this region, though it contains immobile positive and negative ions.

Q6. What is the effect of forward biasing and reverse biasing of a diode on the width of the depletion region?

Ans 1: When forward biased, the width of the depletion region decreases, and when reverse biased, the width of the depletion region increases.

Q7. How does the motion of an electron in an n-type substance differ from the motion of holes in a p-type substance?

Ans 1: Electrons are more mobile and move more rapidly than holes in a p-type substance because electrons do not require holes for their motion, but in a p-type substance, holes depend upon electrons for their motion. Both move in opposite directions.

Q8. Give any two characteristics of operational amplifier.

Ans 1: Input Resistance: It is the resistance between the + and - input of the amplifier, whose value is of the order of several mega ohms.
Output resistance: It is the resistance between the output terminal and ground. Its value is only a few ohms.

Q9. Differentiate between the forward biased and the reverse biased.

Ans 1: When p side is positive and n-side is negative, the diode is forward biased. The width of depletion region reduces to which more current is allowed to flow across the junction. The forward resistance is few ohms.

Ans 2: When p side is negative and n side is positive, the diode is reverse biased. The width of depletion region is increased and a very small current flows across the junction due to flow of minority charge carriers. The resistance offered by the diode is several mega ohms.

Q10. How is the XOR gate so called?

Ans 1: One of its most commonly used applications is as a basic logic comparator which produces a logic "1" output when its two input bits are not equal. Because of this, the XOR gate has an inequality status being known as an odd function.
